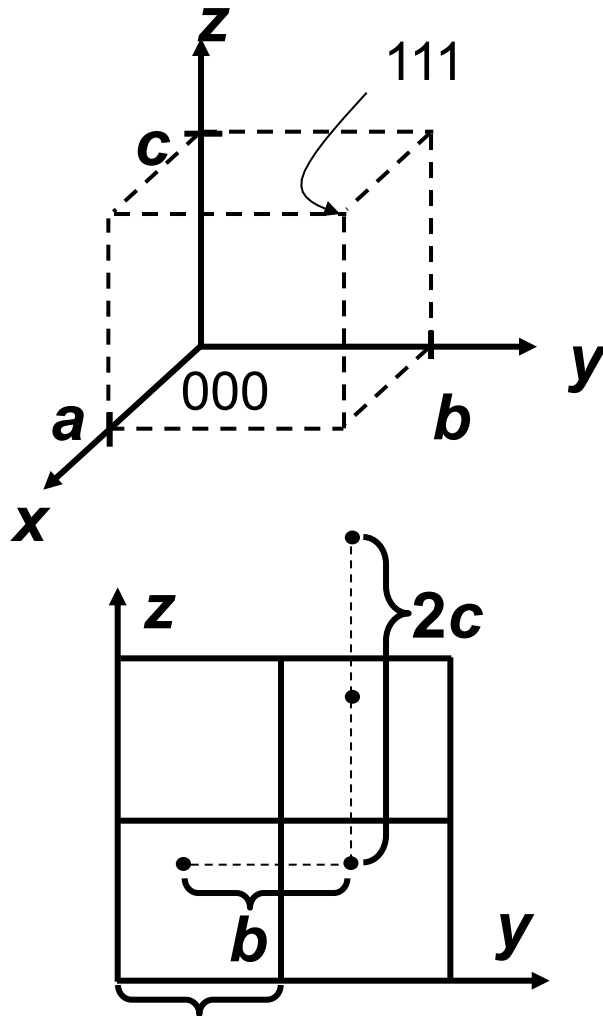


Point coordinates

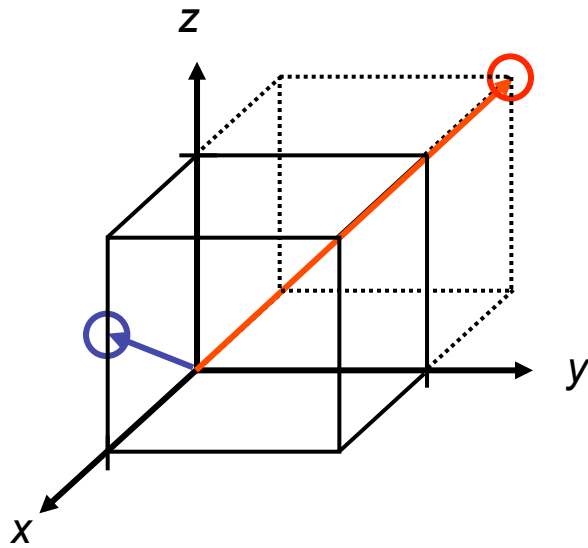


- Point coordinates for unit cell center are

$$a/2, b/2, c/2 \quad \frac{1}{2} \frac{1}{2} \frac{1}{2}$$

- Point coordinates for unit cell corner are 111
- Translation: integer multiple of lattice constants \rightarrow identical position in another unit cell

Directions



Algorithm

1. Vector repositioned (if necessary) to pass through origin.
2. Read off projections in terms of unit cell dimensions a , b , and c
3. Adjust to smallest integer values
4. Enclose in square brackets, no commas
[xyz]

ex: $1, 0, \frac{1}{2} \Rightarrow 2, 0, 1 \Rightarrow [201]$

$-1, 1, 1 \Rightarrow [\bar{1}11]$ where overbar represents a negative index

families of directions $\langle xyz \rangle$

Crystallographic planes

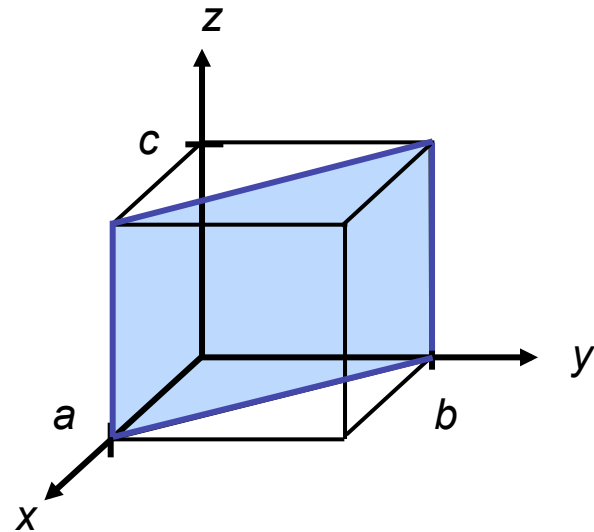
Miller Indices: Reciprocals of the (three) axial intercepts for a plane, cleared of fractions & common multiples. All parallel planes have same Miller indices.

Algorithm

1. Read off intercepts of plane with axes in terms of a , b , c
2. Take reciprocals of intercepts
3. Reduce to smallest integer values
4. Enclose in parentheses, no commas i.e., (hkl)

example

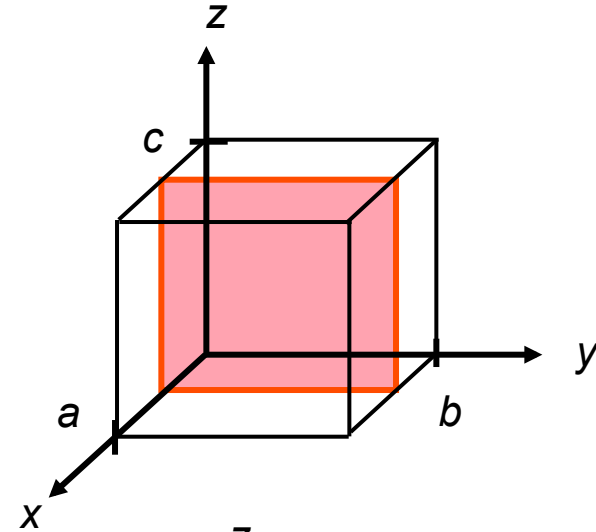
	a	b	c
1. Intercepts	1	1	∞
2. Reciprocals	$1/1$	$1/1$	$1/\infty$
3. Reduction	1	1	0
4. Miller Indices	(110)		



Crystallographic planes

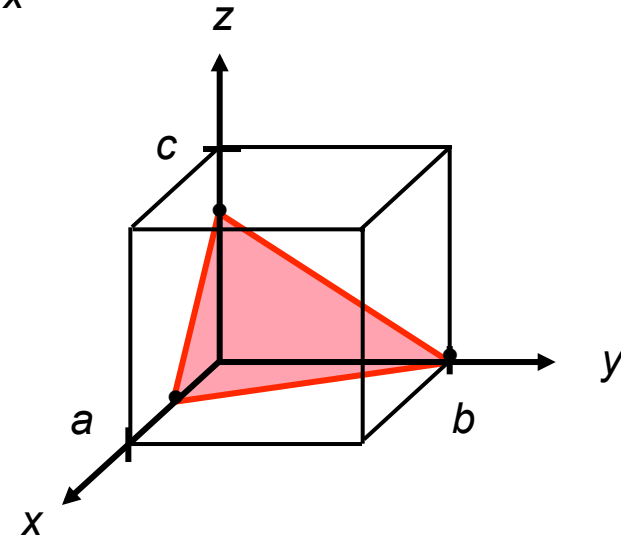
example

	<i>a</i>	<i>b</i>	<i>c</i>
1. Intercepts	1/2	∞	∞
2. Reciprocals	1/1/2	1/ ∞	1/ ∞
	2	0	0
3. Reduction	2	0	0
4. Miller Indices	(200)		



example

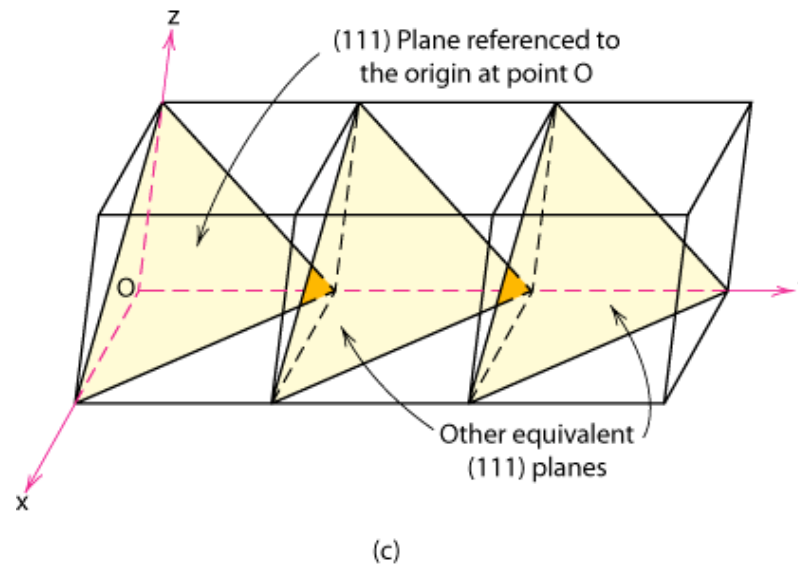
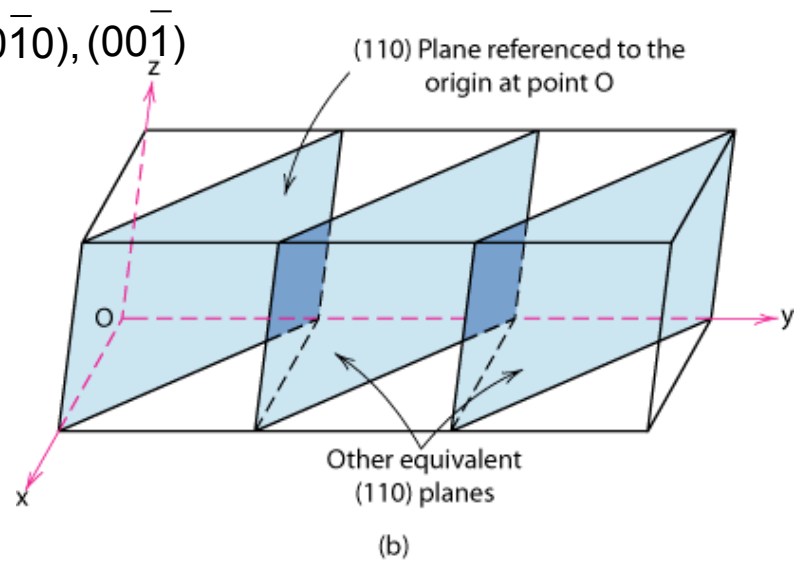
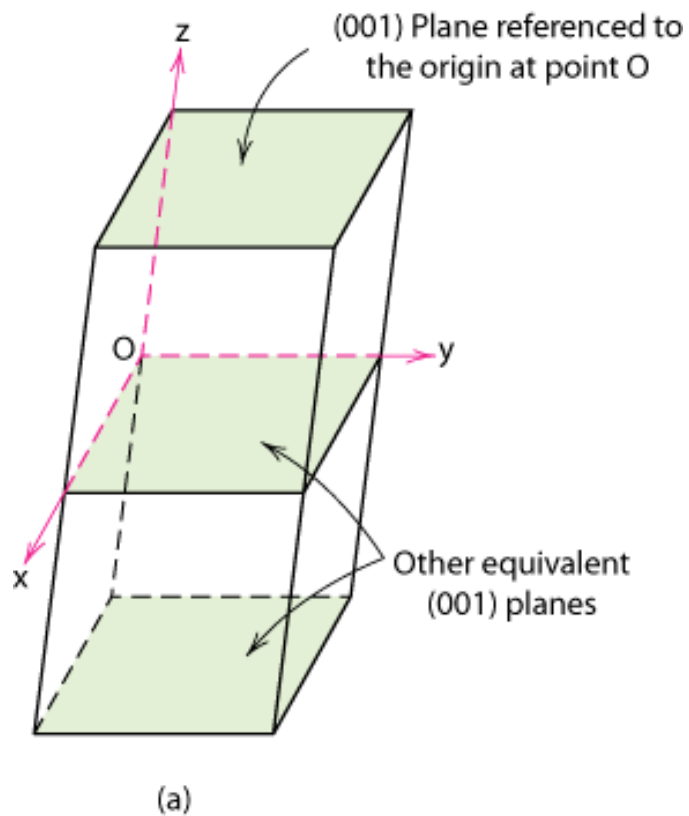
	<i>a</i>	<i>b</i>	<i>c</i>
1. Intercepts	1/2	1	3/4
2. Reciprocals	1/1/2	1/1	1/3/4
	2	1	4/3
3. Reduction	6	3	4
4. Miller Indices	(634)		



Crystallographic planes

Family of Planes $\{hkl\}$

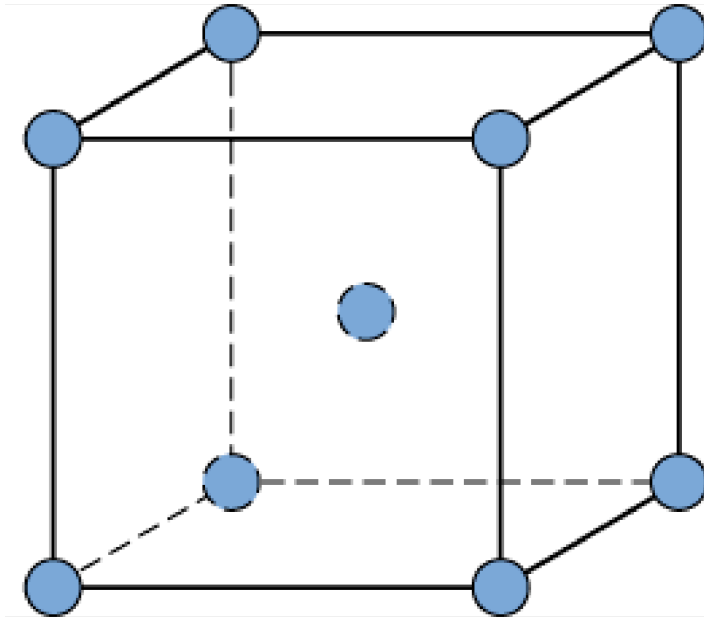
Ex: $\{100\} = (100), (010), (001), (\bar{1}00), (0\bar{1}0), (00\bar{1})$



Adapted from Fig. 3.9, *Callister 7e*.

Linear density: BCC

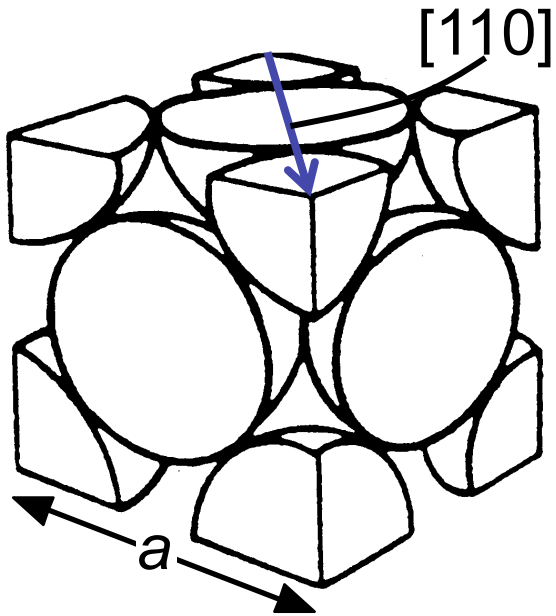
$$\text{Linear Density of Atoms} \equiv \text{LD} = \frac{\text{Number of atoms}}{\text{Unit length of direction vector}}$$



$$[100]: \text{LD} = \frac{1}{a} = \frac{\sqrt{3}}{4R}$$

$$[111]: \text{LD} = \frac{2}{4R} = \frac{1}{2R}$$

Linear density (FCC) and planar density



ex: linear density of Al in $[110]$ direction
 $a = 0.405 \text{ nm}$

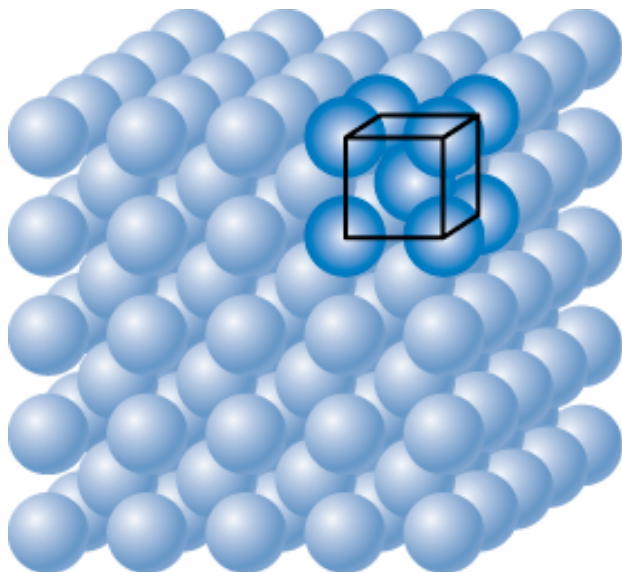
$$\text{LD} = \frac{\text{\# atoms}}{\text{length}} = \frac{2}{\sqrt{2} a} = 3.5 \text{ nm}^{-1}$$

The number 2 is highlighted in a green box, and the term $\sqrt{2} a$ is highlighted in a blue box. The final result, 3.5 nm^{-1} , is highlighted in a yellow box.

$$\text{Planar Density of Atoms} \equiv \text{PD} = \frac{\text{Number of atoms}}{\text{Area of plane}}$$

Planar density

- We want to examine the atomic packing of crystallographic planes
 - Iron foil can be used as a catalyst. The atomic packing of the exposed planes is important.
 - a) Draw (100) and (111) crystallographic planes for Fe.
 - b) Calculate the planar density for each of these planes.
- $R = 0.1241 \text{ nm}$ and Fe has a BCC structure at room temperature



Adapted from Fig. 3.2(c), *Callister 7e*.

2D repeat unit

$$a = \frac{4\sqrt{3}}{3}R$$

atoms

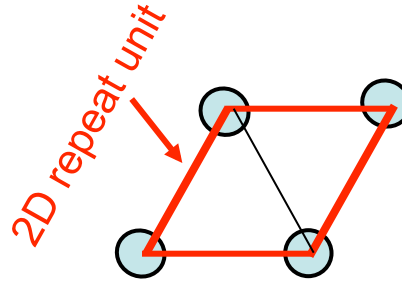
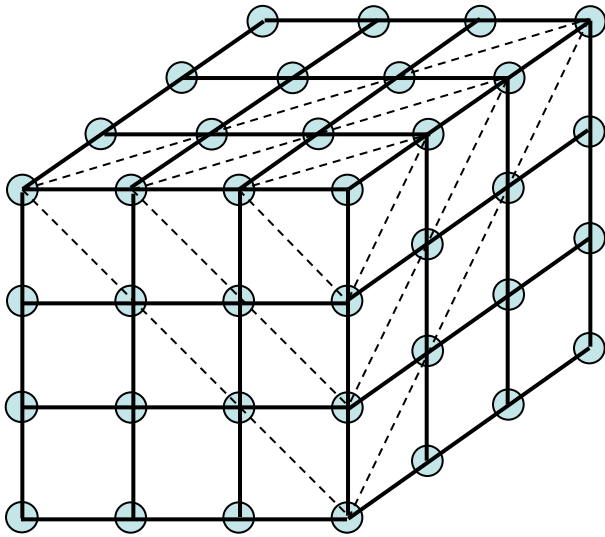
2D repeat unit

Planar Density = $\frac{\text{atoms}}{\text{area of 2D repeat unit}}$

$$= \frac{1}{\left(\frac{4\sqrt{3}}{3}R\right)^2}$$

$$= 1.2 \times 10^{19} \frac{\text{atoms}}{\text{m}^2}$$

Planar density



$$\text{area} = \sqrt{2} ah = \sqrt{3} a^2 = \sqrt{3} \left(\frac{4\sqrt{3}}{3} R \right)^2 = \frac{16\sqrt{3}}{3} R^2$$

atoms
 2D repeat unit

Planar Density =

area
 2D repeat unit

$$= \frac{1}{\frac{16\sqrt{3}}{3} R^2} = 7.0 \frac{\text{atoms}}{\text{nm}^2} = 0.70 \times 10^{19} \frac{\text{atoms}}{\text{m}^2}$$

Single crystal vs. Polycrystalline structures

Single crystals: Atoms all have the same arrangement throughout.

Polycrystalline: Many crystals put together.



Anisotropic

Adapted from Fig. K, color inset pages of *Callister 5e*.
(Fig. K is courtesy of Paul E. Danielson, Teledyne Wah Chang Albany)

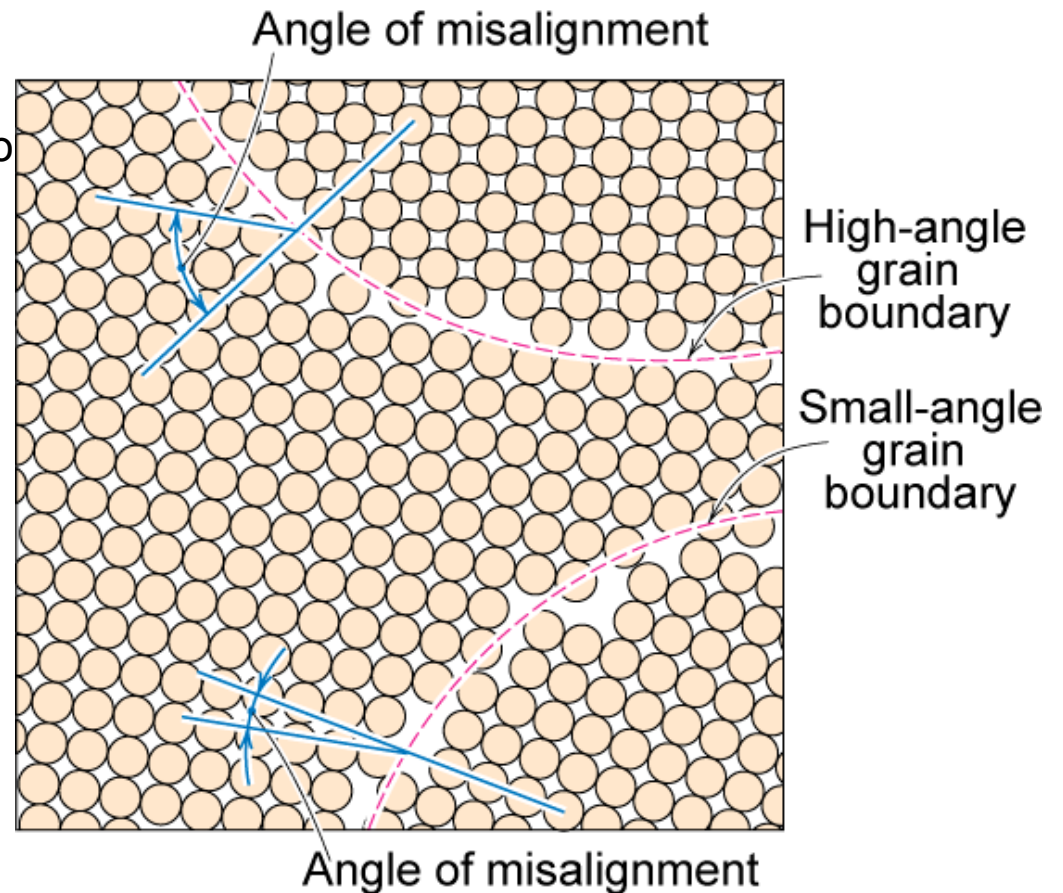
Isotropic

- Nb-Hf-W plate with an electron beam weld.
- Each "grain" is a single crystal.
- If grains are randomly oriented, overall component properties are not directional.
- Grain sizes typ. range from 1 nm to 2 cm (i.e., from a few to millions of atomic layers).

Polycrystalline structures

Grain Boundaries

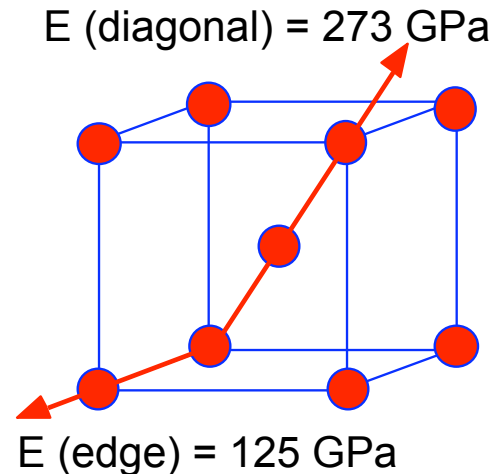
- regions between crystals
- transition from lattice of one region to that of the other
- slightly disordered
- low density in grain boundaries
 - high mobility
 - high diffusivity
 - high chemical reactivity



Adapted from Fig. 4.7, *Callister 7e*.

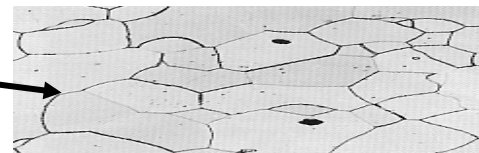
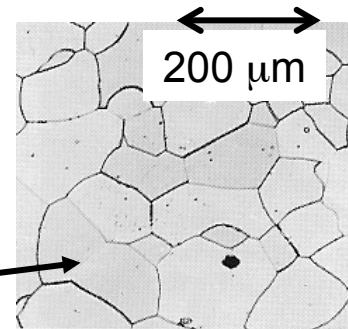
Single crystal vs. Polycrystalline structures

- Single Crystals
 - Properties vary with direction: **anisotropic**.
 - Example: the modulus of elasticity (E) in BCC iron:



Data from Table 3.3, *Callister 7e*.
(Source of data is R.W. Hertzberg, *Deformation and Fracture Mechanics of Engineering Materials*, 3rd ed., John Wiley and Sons, 1989.)

- Polycrystals
 - Properties may/may not vary with direction.
 - If grains are randomly oriented: **isotropic**. ($E_{\text{poly iron}} = 210$ GPa)
 - If grains are **textured**, anisotropic.

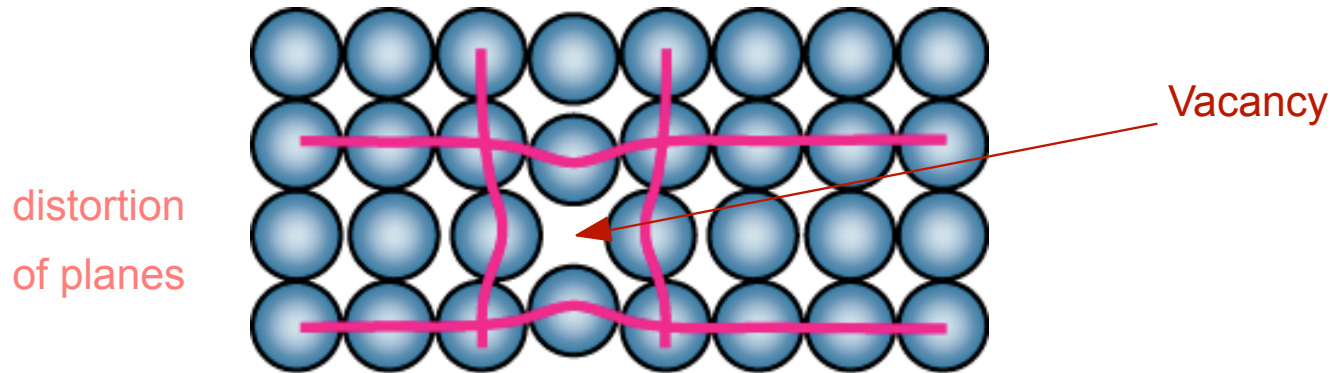


Adapted from Fig. 4.14 (b), *Callister 7e*.
(Fig. 4.14(b) is courtesy of L.C. Smith and C. Brady, the National Bureau of Standards, Washington, DC [now the National Institute of Standards and Technology, Gaithersburg, MD].)

Point defects

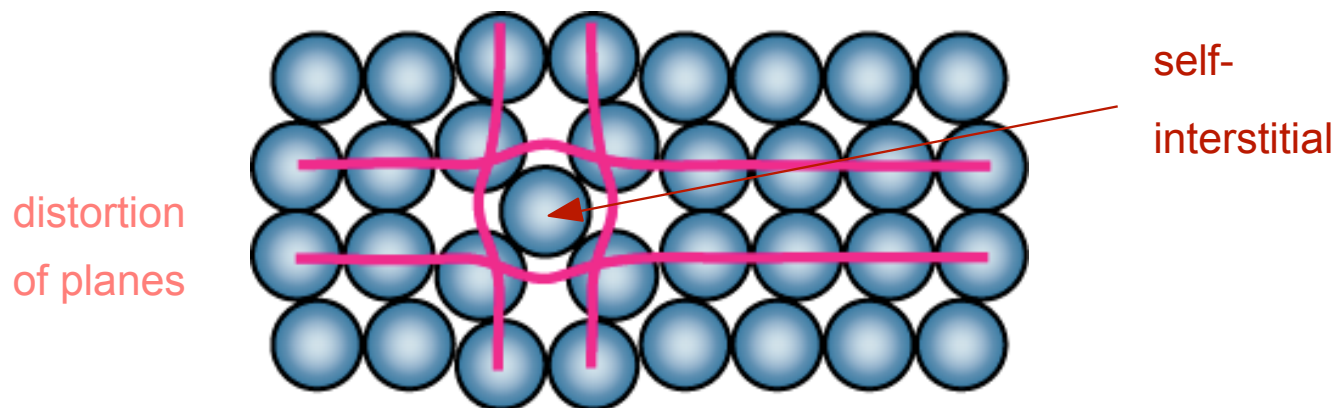
- Vacancies:

-vacant atomic sites in a structure.



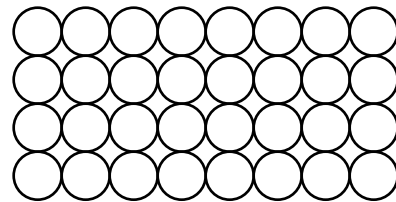
- Self-Interstitials:

- "extra" atoms positioned between atomic sites.



Equilibrium concentration of defects

- Equilibrium concentration varies with temperature



Each lattice site is a potential vacancy

No. of defects

No. of potential defect sites.

$$\frac{N_v}{N} = \exp\left(\frac{-Q_v}{kT}\right)$$

Activation energy

Boltzmann's constant

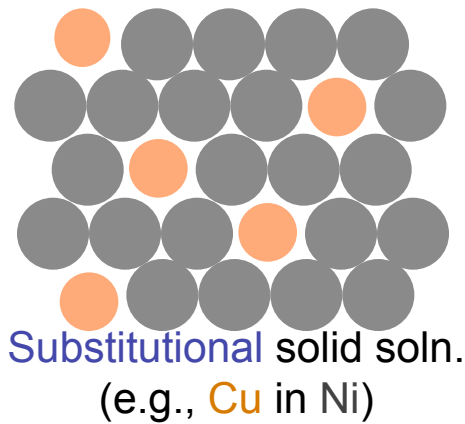
Temperature

Detailed description: The diagram illustrates the Arrhenius equation for the equilibrium concentration of vacancies. On the left, a blue arrow points from the text 'No. of defects' to the numerator N_v of the fraction $\frac{N_v}{N}$. A black arrow points from the text 'No. of potential defect sites.' to the denominator N . The fraction is followed by an equals sign and the exponential function $\exp\left(\frac{-Q_v}{kT}\right)$. A red arrow points from the text 'Activation energy' to the $-Q_v$ term in the numerator of the exponent. A green arrow points from the text 'Boltzmann's constant' to the k in the denominator. A yellow arrow points from the text 'Temperature' to the T in the denominator.

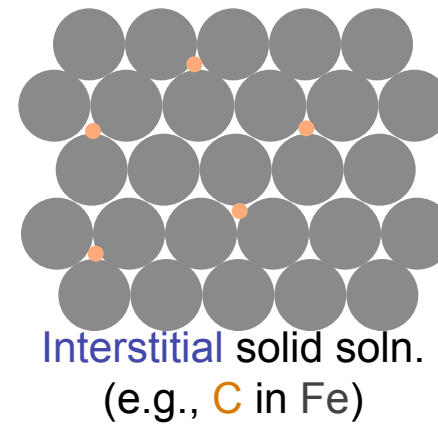
Point defects in alloys

Two outcomes if impurity (B) added to host (A):

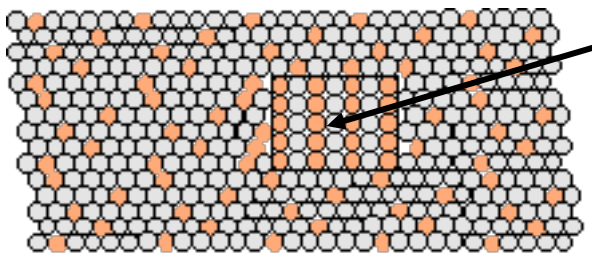
- **Solid solution** of B in A (i.e., random dist. of point defects)



OR



- Solid solution of B in A plus particles of a new phase (usually for a larger amount of B)



Second phase particle
--different **composition**
--often different structure.

Imperfections of solids

Conditions for substitutional solid solution (S.S.)

W. Hume – Rothery rule

1. Δr (atomic radius) < 15%
2. Proximity in periodic table
i.e., similar electronegativities
3. Same crystal structure for pure metals
4. Valency

All else being equal, a metal will have a greater tendency to dissolve a metal of higher valency than one of lower valency

1. Would you predict more Al or Ag to dissolve in Zn?
2. More Zn or Al in Cu?

<i>Element</i>	<i>Atomic Radius (nm)</i>	<i>Crystal Structure</i>	<i>Electro-negativity</i>	<i>Valence</i>
Cu	0.1278	FCC	1.9	+2
C	0.071			
H	0.046			
O	0.060			
Ag	0.1445	FCC	1.9	+1
Al	0.1431	FCC	1.5	+3
Ni	0.1246	FCC	1.8	+2
Zn	0.1332	HCP	1.6	+2

Table on p. 106, *Callister 7e.*

Line defects

- Linear Defects (**Dislocations**)
 - Are one-dimensional defects around which atoms are misaligned
- **Edge dislocation**:
 - extra half-plane of atoms inserted in a crystal structure
 - $\mathbf{b} \perp$ to dislocation line
- **Screw dislocation**:
 - spiral planar ramp resulting from shear deformation
 - $\mathbf{b} \parallel$ to dislocation line

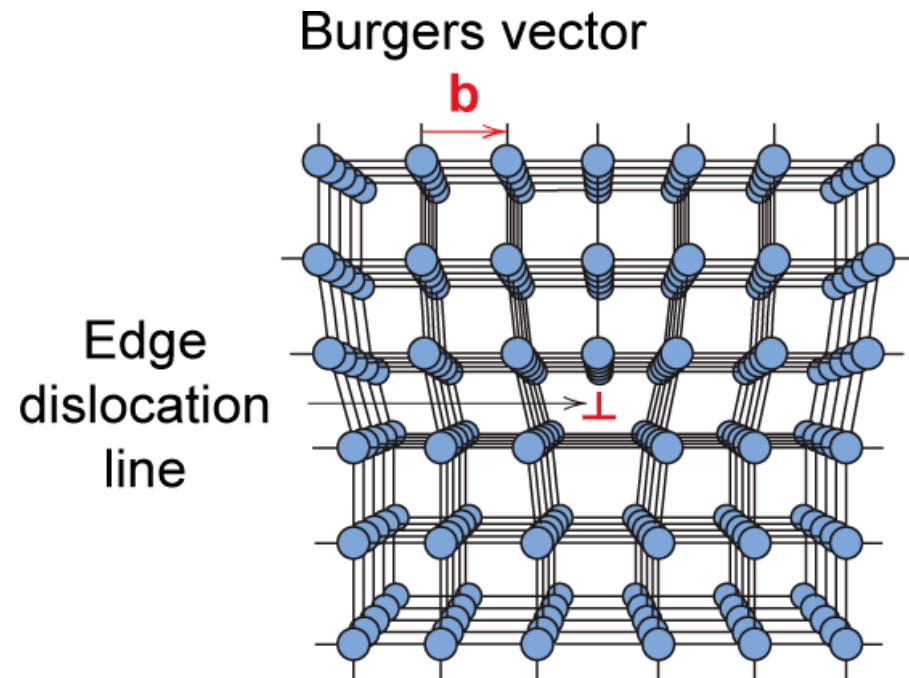
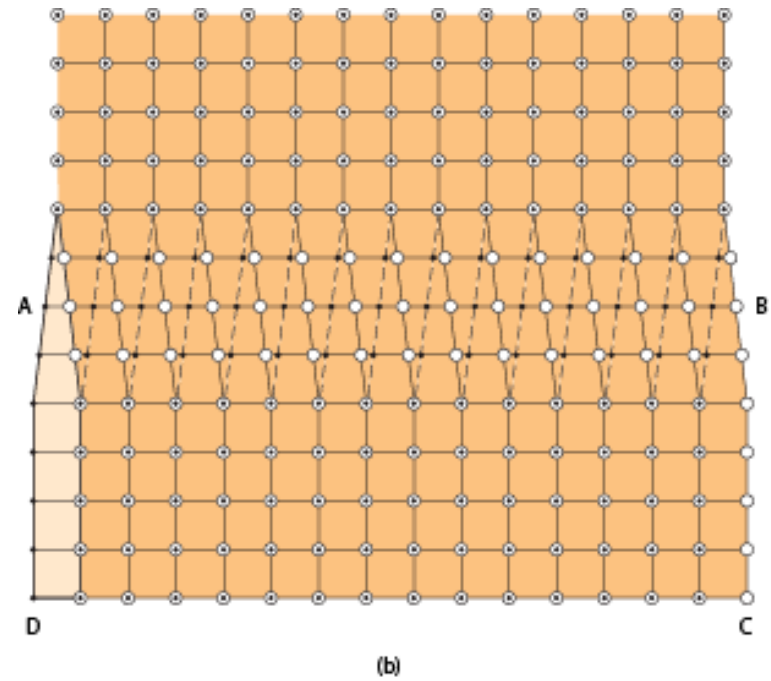
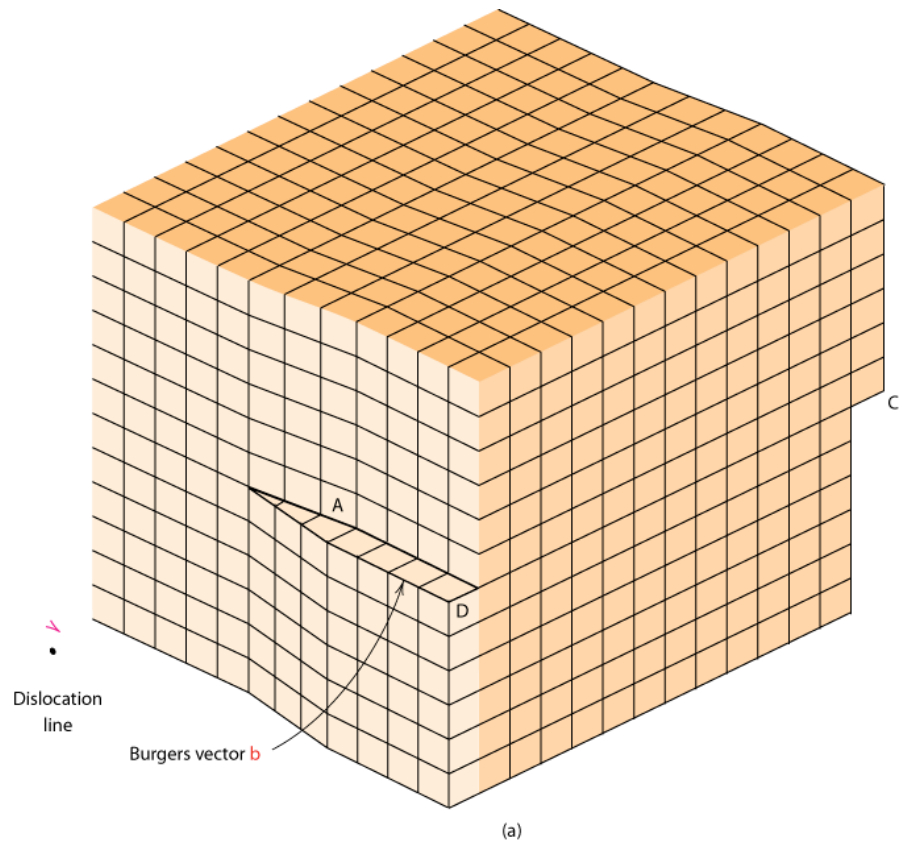


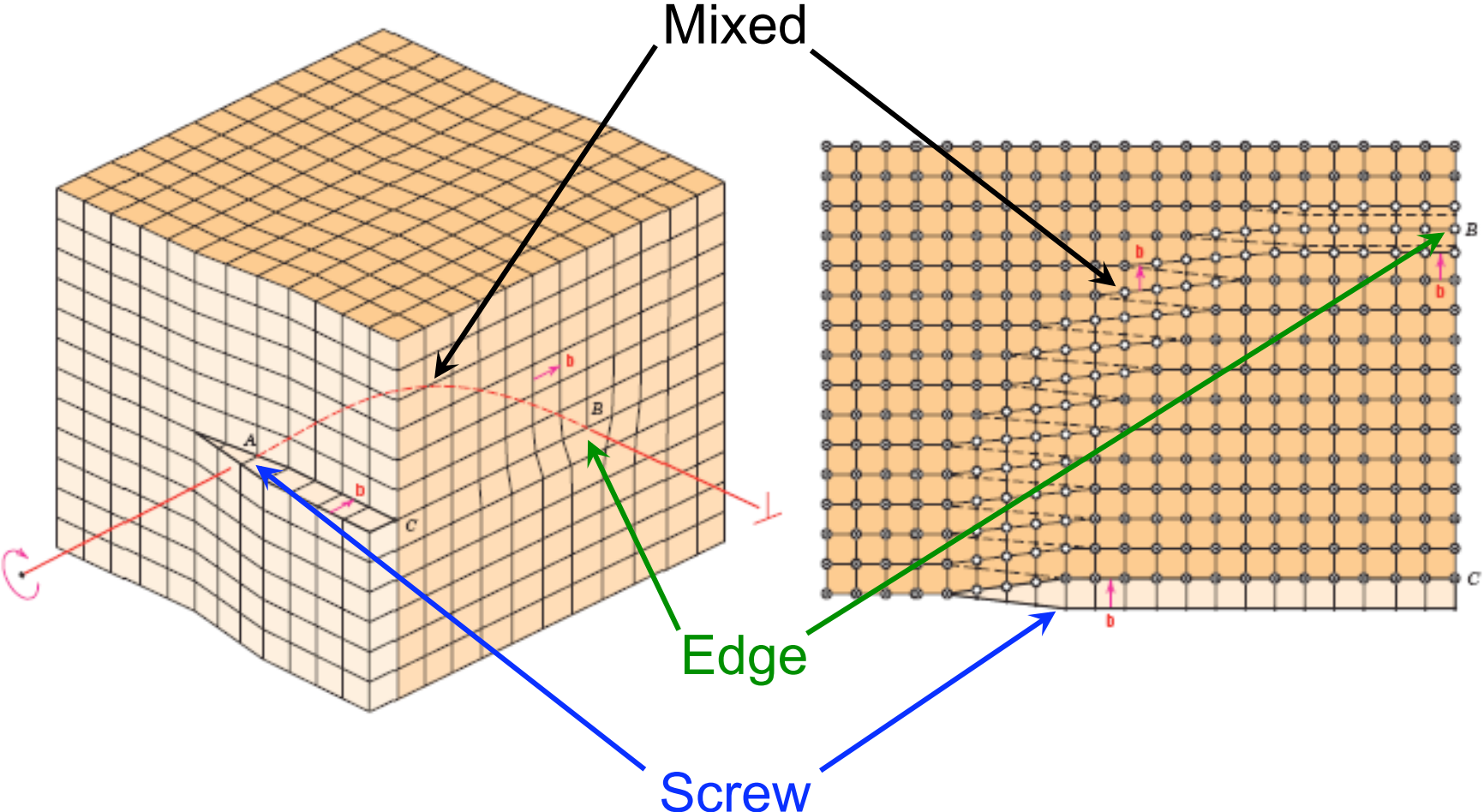
Fig. 4.3, Callister 7e.

Screw defects



Adapted from Fig. 4.4, *Callister 7e*.

Mixed defects

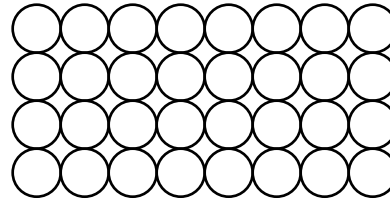


Adapted from Fig. 4.5, Callister 7e.

Planar defects

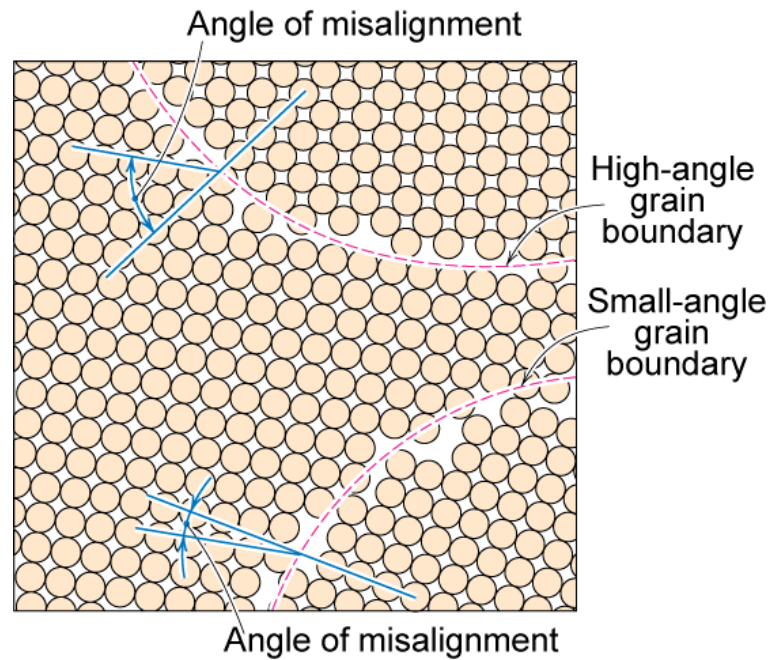
- External defects

- On the surface
- Unsatisfied bonds



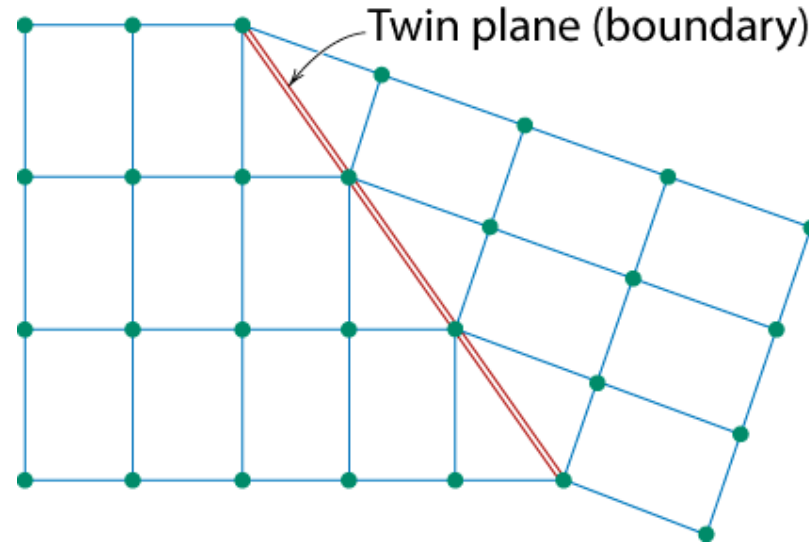
- Internal defects

- Grain boundaries



Planar defects

- **Twin boundary (plane)**
Essentially a reflection of atom positions across the **twin plane**.



Adapted from Fig. 4.9, *Callister 7e*.

- **Stacking faults**
For FCC metals an error in ABCABC packing sequence
Ex: ABCABABC